

Power Transistors

2SD2137A

FEATURES

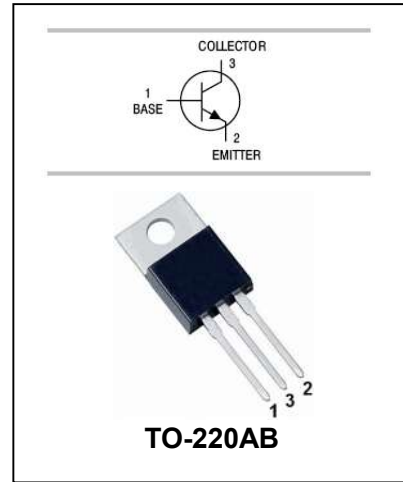
- High Forward Current Transfer Ratio h_{FE} Which Has Satisfactory Linearity.
- Low Collector-emitter Saturation Voltage $V_{CE(sat)}$.
- Allowing Supply With The Radial Taping.



Lead-free

APPLICATIONS

- For Power Amplification.
- Complementary to 2SB1417A.



MAXIMUM RATING operating temperature range applies unless otherwise specified

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	80	V
V_{CEO}	Collector-Emitter Voltage	80	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current	3	A
I_{CP}	Peak Collector Current	5	A
P_C	Collector Dissipation	15 2	W
T_j, T_{stg}	Junction and Storage Temperature	-55 to +150	°C

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ELECTRICAL CHARACTERISTICS Ratings at 25°C ambient temperature unless otherwise specified.

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-Emitter Voltage	V_{CEO}	$I_C=30mA, I_B=0$	80			V
Base-Emitter Voltage	V_{BE}	$V_{CE}=4V, I_C=3A$			1.8	V
Collector Cut-off Current	I_{CEO}	$V_{CE}=60V, I_B=0$			100	μA
Collector Cut-off Current	I_{CES}	$V_{CE}=80V, V_{BE}=0$			100	μA
Emitter Cut-off Current	I_{EBO}	$V_{EB}=6V, I_C=0$			100	μA
DC Current Gain	h_{FE}	$V_{CE}=4V, I_C=1A$	70		320	
		$V_{CE}=4V, I_C=3A$	10			
Collector-emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=3A, I_B=375mA$			1.2	V
Transition Frequency	f_T	$V_{CE}=5V, I_C=0.2A$ $f=10MHz$		30		MHz
Turn-on Time	t_{on}	$I_C=1A, I_{B1}=0.1A,$ $I_{B2}=-0.1A,$ $V_{CC}=50V$		0.3		μs
Storage Time	t_{stg}			2.5		μs
Fall Time	t_f			0.2		μs

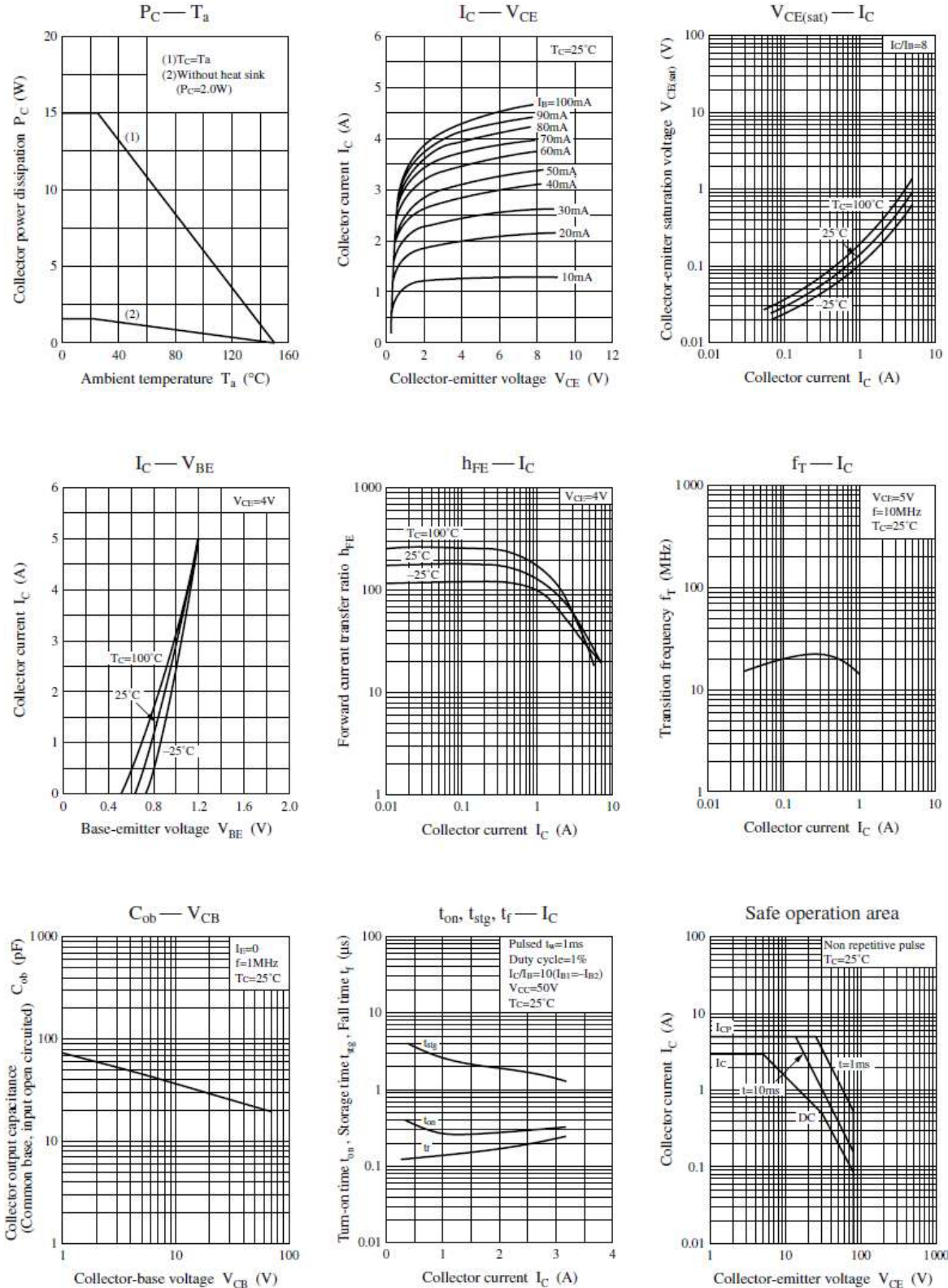
CLASSIFICATION OF h_{FE}

Rank	Q	P	Q
Range	70-150	120-250	160-320

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TYPICAL CHARACTERISTICS @ $T_a=25^\circ\text{C}$ unless otherwise specified



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PACKAGE OUTLINE

Plastic surface mounted package

TO-220AB

